



Sharp Interface Capturing Methods

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> Introduction: challenges for free boundary problems

- > Keep track of a moving front
- > Efficiently capture small scales
- > Impose boundary conditions at the front







► Keep track of a moving front --> Level-Set Representation







► Impose boundary conditions at the front --> Sharp Approach



$\Delta u = F$	$\mathbf{x} \in \Omega^{-},$
u = G	on $\phi^D = 0$,
$\frac{\partial u}{\partial n} = K$	on $\phi^N = 0$,
$\frac{\partial u}{\partial n} + \alpha u = M$	on $\phi^R = 0$,











- ► Impose boundary conditions at the front --> Sharp Approach
- > Interested in macroscale simulations







- ► Impose boundary conditions at the front --> Sharp Approach
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> Efficiently capture small scales --> Adaptive Mesh Refinement







PART I:

Adaptive Quadtree/Octree Grids





> FEM: Many pros - mesh generation challenging



- Test functions, IBP, ...
- Approximate the space
- Impose BC easily
- Leads to SPD







- > AMR: Many pros block structures consume CPU and memory
 - Approximate the operator



- Impose BC harder
- Advantages in parallelization







Tree grids: Rather recent - versatile
 reduce number of nodes









Level=0





























> Tree grids: refine near the free boundary



 $\min_{v \in \text{vertices}(C)} |\phi(v)| \le \text{Lip}(\phi) \cdot \text{diag-size}(C)$







> Cell structure: choice of data location







> Definition at T-junction nodes

- > Existing approaches: Aftosmis, Losasso, ... : Cell based FV.
- > Present approach: Node based (pros for level-set methods [Strain])







Definition at T-junction nodes







Definition at T-junction nodes







> Definition at T-junction nodes



► Use derivative in the transversal direction – always possible for node-based grids

- > Third-order accurate interpolation
- > Only uses 2 (adjacent) cells





Definition at T-junction nodes



> Use derivative in the transversal direction - always possible for node-based grids

> Third-order accurate interpolation

Only uses 3 (adjacent) cells





> Application to solving the Poisson equation

- ► Linear system non-symmetric
 - > M-matrix, thus invertible
- Second-order accurate solutions in max norm
- Second-order accurate gradient in max norm



$$\Omega = [0,\pi]^2$$
$$u(x,y) = e^{-x-y}$$

$ u-u_h _{\infty}$	Order	$ \nabla u - \nabla u_h _{\infty}$	order
7.04×10^{-3}	—	3.42×10^{-2}	—
1.74×10^{-3}	2.01	1.41×10^{-2}	1.28
3.97×10^{-4}	2.13	4.38×10^{-3}	1.68
9.33×10^{-5}	2.09	1.18×10^{-3}	1.89
2.26×10^{-5}	2.05	$3.09 imes 10^{-4}$	1.93
	$\begin{aligned} u - u_h _{\infty} \\ 7.04 \times 10^{-3} \\ 1.74 \times 10^{-3} \\ 3.97 \times 10^{-4} \\ 9.33 \times 10^{-5} \\ 2.26 \times 10^{-5} \end{aligned}$	$ u - u_h _{\infty}$ Order 7.04×10^{-3} - 1.74×10^{-3} 2.01 3.97×10^{-4} 2.13 9.33×10^{-5} 2.09 2.26×10^{-5} 2.05	$\begin{array}{c c c c c c c c c c c c c c c c c c c $





> Application to Stefan problems

> Diffusion dominated phenomena

> Used in modeling solidification processes, epitaxial growth...







PART II:

Mixed Boundary Conditions

At

Irregular and Free Boundaries





> Imposing Boundary Conditions

► Locally uniform near the interface







> Mixed boundary conditions: Dirichlet-Neumann-Robin

> Implicit representation of the domain – Applicable to moving boundaries



 $\begin{aligned} \Delta u &= F & \mathbf{x} \in \Omega^{-}, \\ u &= G & \text{on } \phi^{D} &= 0, \\ \frac{\partial u}{\partial n} &= K & \text{on } \phi^{N} &= 0, \\ \frac{\partial u}{\partial n} &+ \alpha u &= M & \text{on } \phi^{R} &= 0, \end{aligned}$











Neumann and Robin boundary conditions



 $\int_{C_{ij}\cap\Omega^{-}}\Delta u \ d\Omega = \int_{\partial(C_{ij}\cap\Omega^{-})} n \cdot \nabla u \ d\Gamma,$

 $= \int_{\partial C_{ij} \cap \Omega^-} n \cdot \nabla u \ d\Gamma + \int_{\Gamma \cap \Omega^-} n \cdot \nabla u \ d\Gamma$

$$\begin{split} \Delta u &= F, \quad \mathbf{x} \in \Omega^{-}, \\ \frac{\partial u}{\partial n} &= K, \quad \mathbf{x} \in \Gamma^{N}, \\ \frac{\partial u}{\partial n} &+ \alpha u &= M, \quad \mathbf{x} \in \Gamma^{R}. \end{split}$$

$$L_{i,j+\frac{1}{2}}$$

$$L_{i-\frac{1}{2},j}$$

$$C_{ij}$$

$$L_{i+\frac{1}{2},j}$$

$$L_{i,j-\frac{1}{2}}$$

$$\Omega^{-}$$

$$\Gamma$$





Neumann and Robin boundary conditions

$$\begin{split} \Delta u &= F, \quad \mathbf{x} \in \Omega^{-}, \\ \frac{\partial u}{\partial n} &= K, \quad \mathbf{x} \in \Gamma^{N}, \\ \frac{\partial u}{\partial n} &+ \alpha u = M, \quad \mathbf{x} \in \Gamma^{R}. \end{split}$$

 $\int_{\partial (C_{ij} \cap \Omega^{-})} n \cdot \nabla u \ d\Gamma \simeq L_{i+\frac{1}{2},j} \frac{u_{i+1,j} - u_{i,j}}{\Delta x}$

 $-L_{i-\frac{1}{2},j}\frac{u_{i,j}-u_{i-1,j}}{\Delta x}$

 $+L_{i,j+\frac{1}{2}}\frac{u_{i,j+1}-u_{i,j}}{\Delta y}$

 $-L_{i,j-\frac{1}{2}}\frac{u_{i,j}-u_{i,j-1}}{\Delta y}$













≻ Main features

> SDP - Guarantees stability - Fast solvers



Resolution	$ u-u_h _{\infty}$	Order
32^2	1.67×10^{-3}	
64^2	4.24×10^{-4}	1.98
128^2	1.18×10^{-4}	1.84
256^2	2.89×10^{-5}	2.03



Resolution	$ u-u_h _{\infty}$	Order
16^3	5.74×10^{-2}	
32^{3}	1.66×10^{-2}	1.79
64^3	4.42×10^{-3}	1.91
128^{3}	1.06×10^{-3}	2.06




PART III:

LEVEL-SET TECHNOLOGY CURVATURES

GRAIN GROWTH







Automatic changes in topology but less accurate





> Level-set evolution equation

$$\phi_t + V_n |\nabla \phi| = 0$$

► Method of lines

$$\frac{d\phi}{dt} + V_n \cdot H_G(\phi) = 0$$

► Godunov approximation of the Hamiltonian

$$H_{G}(\phi) = \begin{cases} \sqrt{\max\left(|(D_{x}^{+}\phi)^{-}|^{2}, |(D_{x}^{-}\phi)^{+}|^{2}\right) + \max\left(|(D_{y}^{+}\phi)^{-}|^{2}, |(D_{y}^{-}\phi)^{+}|^{2}\right)} & \text{if } V_{n} > 0\\ \sqrt{\max\left(|(D_{x}^{+}\phi)^{+}|^{2}, |(D_{x}^{-}\phi)^{-}|^{2}\right) + \max\left(|(D_{y}^{+}\phi)^{+}|^{2}, |(D_{y}^{-}\phi)^{-}|^{2}\right)} & \text{otherwise} \end{cases}$$

► Time evolution: TVD-RK schemes

$$\frac{\phi^{n+1} - \phi^n}{\Delta t} + V_n \cdot H_G(\phi^n) = 0$$

$$\frac{\phi^{n+2} - \phi^{n+1}}{\Delta t} + V_n \cdot H_G(\phi^{n+1}) = 0$$

$$\phi^{n+1} = \frac{\phi^n + \phi^{n+2}}{2}$$





> Application to the level-set method

► Loss of volume in level-set methods



> Adaptivity balances volume conservation with CPU efficiency





> Nonlinear effects









Computations are sensitive to noise









► Reinitialization equation

$$\phi_t + \operatorname{Sign}(\phi) |\nabla \phi| = 1$$

► HJ-WENO scheme --> Fifth order accurate

➤ Gibou-Fedkiw (JCP 2005) --> Show that it is second-order accurate

















































- ► Rarefaction wave solution (DuChene-Gibou JSC 2009)
 - ► Fourth-order accurate reinitialization equation
 - ► Second-order accurate curvatures







- ➤ DuChene Gibou (JSC 2009)
- ► Fourth-order accurate reinitialization equation
 - ► Second-order accurate curvatures











- ➤ DuChene Gibou (JSC 2009)
- ► Fourth-order accurate reinitialization equation
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STANDARD LEVEL-SET METHOD

DUCHENE-GIBOU





> Grain Growth

- > Occurs during heat treatment of polycrystalline materials
- > The grain boundaries evolve to reduce the total free energy
- > Minimize the total area
- ► Triple junctions
- Driving force ~ curvature

$$f = \mu \gamma(\theta) \kappa$$







➤ Grain Growth

- Level-Set treatment possible
 - Uniform grids (local level-set?)
 - N level-sets --> N phases
- ➤ Ongoing effort
 - Adaptive grids
 - ${\cal O}(10)$ level-sets --> ${\cal O}(10^6)$ phases







> Grain Growth - 2D

- > 2 level-set functions represent 4 grains
- > Exterior grains cause interior grains to shrink

$$\frac{dA}{dt} = 2\pi\gamma\left(\frac{3}{6} - 1\right)$$







> Grain Growth - 2D

Comparison to Von-Neumann/Mullins law







> Grain Growth - 3D

- > 3 level-set functions represent 5 grains
- > One grain cut away in video so inner grain is visible
- Reuleaux tetrahedron satisfies

$$\frac{d}{dt}V^{2/3} \approx 5.2885$$







> Grain Growth - 3D

> Comparison to Theory







PART IV:

Application to Solidification of Binary Alloys





> Application to the Solidification of Binary Alloys

> Diffusion equations:

$$\begin{array}{lll} \partial T/\partial t &=& \lambda \Delta T & \forall \boldsymbol{x} \in \Omega, \\ \partial C^{l}/\partial t &=& D^{l} \Delta C^{l} & \forall \boldsymbol{x} \in \Omega^{l}, \end{array}$$

$$\partial C^s / \partial t = D^s \Delta C^s \quad \forall \boldsymbol{x} \in \Omega^s,$$



> Diffusion in the solid phase can be neglected

 $(D^s \ll D^l)$

Convection effects are neglected here





> Interface Conditions

> Continuity of the temperature field

$$[T]_{|_{\Gamma}} = 0$$

► Heat flux balance

$$V_n = \frac{k}{L} \left[\frac{\partial T}{\partial n} \right]_{\Gamma} = \frac{k}{L} \left(\frac{\partial T^s}{\partial n} - \frac{\partial T^l}{\partial n} \right)$$

► Gibbs-Thompson relations

$$T_{\mid \Gamma} = T_m + m_L C^l + \epsilon_c(\theta) \kappa + \epsilon_v V_n$$

► Solute rejection equation

$$V_n(C^s - C^l) = D^s \frac{\partial C^s}{\partial n} - D^l \frac{\partial C^l}{\partial n}$$

> Jump in the concentration

$$C^s = k_p C^l$$



CONCENTRATION PROFILE NEAR INTERFACE





> Application to the Solidification of Binary Alloys

► Ni-Cu

► Ignore Convective Effects





SHARP CONCENTRATION PROFILE





> Solving for the temperature field:

> Problem:

$$\begin{array}{rcl} \displaystyle \frac{\partial T}{\partial t} &=& \lambda \Delta T & \quad x \in \Omega \\ \displaystyle [T] &=& 0 & \quad x \in \Gamma \\ \displaystyle \frac{\partial T}{\partial n} \end{array} \end{array} = \begin{array}{rcl} \displaystyle \frac{LV_N}{k} & \quad x \in \Gamma \end{array}$$

> Time Discretization:

$$\frac{T^{n+1} - T^n}{\Delta t} = \lambda \frac{\Delta T^{n+1} + \Delta T^n}{2}$$

> Special treatment is needed close to the interface





> Solving for the temperature field:

> Imposing the jump conditions:

•
$$\Delta T_0 = \frac{T_2^s - 2T_0 + T_1}{\Delta x^2} + \frac{T_4^s - 2T_0 + T_3}{\Delta y^2} + O(h^2)$$

•
$$T_2^s = T_2 + [T]_P + \delta_P \left[\frac{\partial T}{\partial n}\right]_P + O(h^2)$$

• $T_2^s = T_2 + [T]_P + \delta_P \left[\frac{\partial T}{\partial n}\right]_P + O(h^2)$

$$I_{4} = I_{4} + [I]_{Q} + 0_{Q} \left[\frac{\partial n}{\partial n}\right]_{Q} + 0 (n)$$









> Solving for the concentration in the liquid phase:

> Time discretization:

$$\frac{C_L^{n+1} - C_L^n}{\Delta t} = D_L \frac{\Delta C_L^{n+1} + \Delta C_L^n}{2} \qquad x \in \Omega^l.$$

> Dirichlet boundary condition:

$$C_L = \frac{T - T_m}{m_L} - \frac{\epsilon_c(\theta)}{m_L} \kappa - \frac{\epsilon_v}{m_L} V_N \qquad x \in \Gamma$$

Close to the interface:

$$C_{xx}(v_0) = \left(\frac{C_I - C_0}{s_I} - \frac{C_0 - C_2}{s_2}\right) \frac{2}{s_I + s_2}$$



> Similar for the concentration in the solid phase





> Computing the normal velocity from the concentration fields:

> Solute rejection equation

$$V_n(C^s - C^l) = D^s \frac{\partial C^s}{\partial n} - D^l \frac{\partial C^l}{\partial n}.$$

► 4 steps calculation:

- 1. The concentration fields are extended over the interface
- 2. The normal gradient are computed
- 3. Compute velocity from the solute rejection equation
- 4. Extrapolate the velocity from the interface to the entire domain

> Time step Definition:

$$\Delta t = \min\left(lpha \frac{\Delta x}{V_{\max}}, \frac{1}{\max\left(|\kappa V_n|\right)}\right)$$





> Recap:

- > Sharp: interface conditions are imposed at the interface at every time step
- ► No drastic time step restriction
- > Tree-grid techniques lead to efficient computations
- > Linear system are solved using a Multigrid method
- > The algorithm scales with the number of nodes
- > Parallelized using OpenMP
- > On a level 10 (max res=1 024) it takes a few hours on an iMac (8cores)





> Validation:

► Solidification of an Ni-Cu alloy







> Stable planar interface:

> Choose cooling parameters so that theoretically the interface is stable



V = 0.01 cm/s $G = 2.15 \times 10^4 K/m$





> Stable planar interface:

> Convergence analysis:







> Stable planar interface:

- > Convergence analysis:
 - > Planar stable interface
 - \blacktriangleright kG >> LV
 - ► Energy balance








> Stable planar interface:

- > Accuracy analysis:
 - ► Total energy:

E(t) = LVht + E(0)







Planar-Cellular-Dendritic transitions



(a)
$$G = 215 \times 10^2$$
 K/cm, $l = .2$ mm







(b)
$$G = 100 \times 10^2$$
 K/cm, $l = .2$ mm



(d) $G = 4 \times 10^2$ K/cm, l = .4 mm





> Planar-Cellular transitions



V = 0.01 cm/s $G = 1 \times 10^4 K/cm$





Cellular-Dendritic transitions



V = 0.01 cm/s $G = 2 \times 10^3 K/cm$





► Solutal boundary layer:

> Theoretical value:

$$\delta_S = 2D^l / V_{\Gamma}$$









Commonly accepted model:

$$Z_1 = AG_S^{-n}V_{\Gamma}^{-m}$$

$$n = 1/2$$
 and $m = 1/4$







> Formation of the secondary arms

► Max level 12 (4 096), V = 0.01 cm/s, G = 1 K/cm, l = 0.3 cm







> Formation of the secondary arms:

















> Secondary arm spacing:







Fundamentals of Solidification equiated dendritic 10^{2} 105 casting fine dendritic 1 V(mm/s) 100 oriented 100 171 10:24/18 D.S. oriented celular 10-2 Je" ODIATO coarse 2. 10-4 10-1 10³ 10 G(K/mm)



FUNDAMENTALS OF SOLIDIFICATION, KURZ AND FISHER

NUMERICAL RESULTS





> Application to solving the Navier-Stokes equations

> Standard projection method (Chorin) based on the Hodge decomposition

$$\begin{aligned} \mathbf{U}^* &= \mathbf{U}^{n+1} + \nabla \psi \\ \nabla \cdot \mathbf{U}^{n+1} &= 0 \end{aligned} \qquad \mathbf{U}^{n+1} = P(\mathbf{U}^*) \end{aligned}$$

> Decomposition at the discrete level $U^* = U + G\phi, \label{eq:u} DU = 0.$

Decomposition at the discrete level

$$DG\phi = DU^*$$

> Oscillation triggered by even-odd decoupling

$$L\widetilde{\phi} = DU^*$$
$$\mathbf{U}^{n+1} = P_{\mathrm{appr}}(U^*) = U^* - G\widetilde{\phi}$$





> Application to solving the Navier-Stokes equations

$$\mathbf{U}^{n+1} = P_{\text{appr}}(\mathbf{U}^*) = \mathbf{U}^* - \mathbf{G}\psi$$

> Stability enforced at the discrete level

 $G = -D^T$ The relation $G = -D^T$ is not discretely satisfied for our adaptive grids







> Projection method - stability and accuracy

► MAC sampling provides stability on uniform grids

















PART V:

Efficient Parallel Computation of Eikonal Equation



Eikonal equation: a core equation in the level-set technology

- Used to "reinitialize" the level-set function
- > Repeated at each time step

> Existing approaches

> TVD schemes - Most accurate but computationally expensive

O(n)

- > Fast Marching Method $O(n \log n)$
- ➤ Fast Sweeping Method -
- > Parallel FSM Zhao et al.
 - > Straightforward Assign each quadrant to different a processor
 - ➤ Plateau for # processors > 2^d in R^d

> The // implementation requires more iterations than the serial one





 $|\nabla \phi| = 1$





> The FSM uses a Godunov upwind differencing scheme on the interior nodes

$$[(u_{i,j}^{new} - u_{xmin})^+]^2 + [(u_{i,j}^{new} - u_{ymin})^+]^2 = f_{i,j}^2 h^2$$
$$u_{xmin} = \min(u_{i-1,j}, u_{i+1,j}) \qquad \text{and} \qquad (x)^+ = \begin{cases} x & x > 0, \\ 0 & x \le 0. \end{cases}$$

> Our approach: different sweeping ordering (Cuthill-McKee)

Level=i+j
Nodes on a level are updated simultaneously
Performance does not plateau
Level = 3







k

3D ·k

≻ Similar idea in 3D

Sweeping ordering in 3D





Load balancing strategy

Divide and merge





> Efficiency

➤ Distance function from a center source point in 3D with four concentric spherical obstacles.













> GPU Computing

- > The existing parallel techniques have very limited parallel speedup.
- > Our method doesn't suffer the same limitations
- ➤ Great speedup results on GPUs
- > Makes larger problems tractable







Conclusions

Sharp treatment for the interface conditions

- > Numerical result agree with theoretical predictions and experimental observations
- Curvature and grain growth

> Future work

> Fluid in solidification, parallel efficiency, grain growth, ...

> Special thanks

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